

Outline Dimensions and Mark

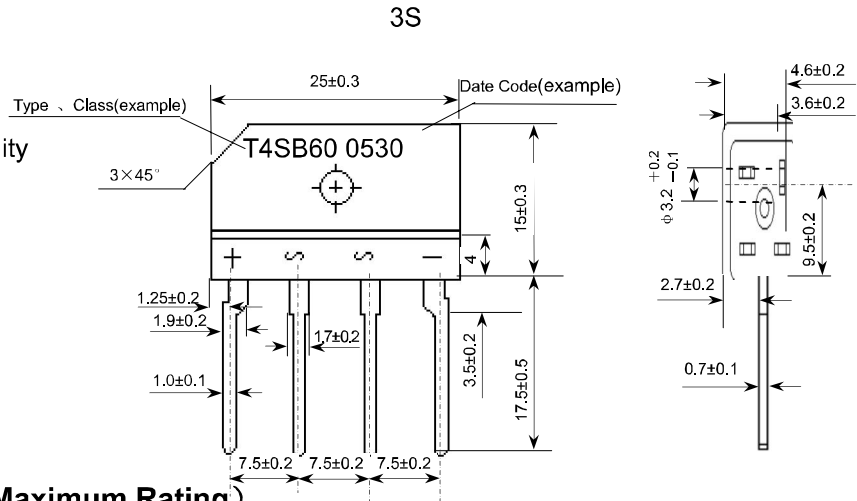
Unit: mm

■ **Features**

- I_o 4.0A
- V_{RRM} 200V~800V
- Glass passivated chip
- High surge forward current capability

■ **Applications**

- General purpose 1 phase Bridge rectifier applications



■ **Limiting Values (Absolute Maximum Rating)**

Item	Symbol	Unit	Conditions	T4SB			
				20	40	60	80
Storage Temperature	T_{stg}	°C		-40 ~ +150			
Junction Temperature	T_j	°C		+150			
Repetitive Peak Reverse Voltage	V_{RRM}	V		200	400	600	800
Average Rectified Output Current	I_o	A	50Hz sine wave, R-load	With Heatsink $T_c=108^\circ\text{C}$			
				Without Heatsink $T_a=25^\circ\text{C}$			
Surge(Non-repetitive)Forward Current	I_{FSM}	A	50Hz sine wave, 1 cycle, $T_a=25^\circ\text{C}$	150			
Current Squared Time	I^2t	A ² s	$1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$, Rating of per diode	93			
Dielectric Strength	Vdis	kV	Terminals to case. AC 1 minute	2			
Mounting Torque	TOR	kg · cm	Recommend torque: 5kg · cm	8			

■ **Electrical Characteristics** ($T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	$I_{FM}=2.0\text{A}$, Pulse measurement, Rating of per diode	0.95
Peak Reverse Current	I_{RRM1}	μA	$V_{RM}=V_{RRM}$, Pulse measurement, Rating of per diode,	10
Thermal Resistance	$R_{\theta J-A}$	°C/W	Between junction and ambient, Without heatsink	30
	$R_{\theta J-L}$		Between junction and lead, Without heatsink	6
	$R_{\theta J-C}$		Between junction and case, With heatsink	5.5

■ **Characteristics(Typical)**

